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## Comparative study of light and thermal induced degradation for both fullerene and non-fullerene based organic solar cells

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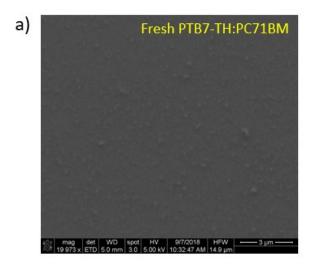
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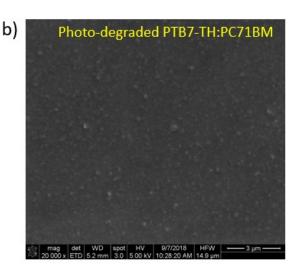
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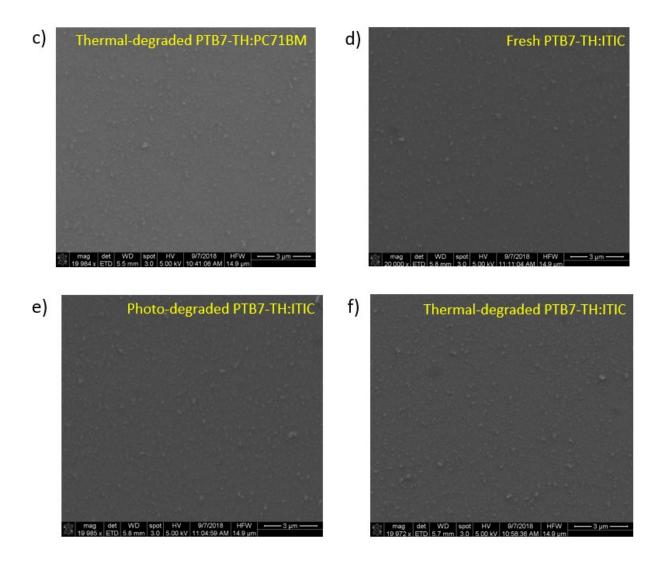
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## **Support information**







**Figure S1.** The SEM images of both PTB7-Th:PC<sub>71</sub>BM fullerene and PTB7-Th:ITIC non-fullerene based fresh, photo-degraded and thermal-degraded blend films deposited on top of ITO/ZnO surface.

**Table S1.** Photovoltaic parameters for 5 hours of continuous light illumination for burn-in photo degradation test measured under one-sun test condition (AM1.5G illumination at 100 mW cm<sup>-2</sup>) for both PTB7-Th:PC<sub>71</sub>BM fullerene and PTB7-Th:ITIC non-fullerene based devices obtained from at least 5 devices.

Degradation Time for PTB7- Th:PC <sub>71</sub> BM Devices	V (V)	J <sub>SC</sub> (mA/cm <sup>2</sup> )	FF	РСЕ	RSH (Ω cm²)	RS (Ω cm²)
Devices	V <sub>oc</sub> (V)	(IIIA/CIII-)	rr	FCE	KSH (22 CIII-)	K5 (22 CIII-)
0Н	0.819±0.001	14.76±0.94	0.62±0.02	7.58±0.50%	573±71	5.72±0.54
1H	0.793±0.003	14.26±0.84	0.60±0.02	6.79±0.50%	514±47	6.05±0.68
2Н	0.786±0.002	13.83±0.78	0.58±0.02	6.29±0.44%	493±46	7.39±0.85
3Н	0.782±0.003	13.92±0.79	0.56±0.03	6.07±0.46%	445±62	8.06±1.10
4H	0.779±0.003	13.41±0.70	0.54±0.03	5.64±0.47%	422±58	8.98±1.37
5H	0.778±0.003	13.13±0.73	0.53±0.03	5.40±0.48%	406±62	9.65±1.60
Degradation Time for PTB7- Th:ITIC Devices	V <sub>oc</sub> (V)	J <sub>SC</sub> (mA/cm <sup>2</sup> )	FF	PCE	RSH (Ω cm <sup>2</sup> )	RS (Ω cm <sup>2</sup> )
Time for PTB7- Th:ITIC	V <sub>OC</sub> (V)		0.60±0.01	PCE 6.72±0.15%	RSH ( $\Omega$ cm <sup>2</sup> ) $648 \pm 51$	RS (Ω cm <sup>2</sup> ) 8.25±0.54
Time for PTB7- Th:ITIC Devices		(mA/cm <sup>2</sup> )			,	
Time for PTB7-Th:ITIC Devices	0.831±0.001	(mA/cm <sup>2</sup> ) 13.46±0.19	0.60±0.01	6.72±0.15%	648 ± 51	8.25±0.54
Time for PTB7-Th:ITIC Devices  0H	0.831±0.001 0.790±0.005	(mA/cm <sup>2</sup> )  13.46±0.19  12.33±0.16	0.60±0.01 0.49±0.02	6.72±0.15% 4.78±0.17%	$648 \pm 51$ $397 \pm 22$	8.25±0.54 10.68±0.45
Time for PTB7-Th:ITIC Devices  0H  1H  2H	0.831±0.001 0.790±0.005 0.788±0.004	(mA/cm <sup>2</sup> )  13.46±0.19  12.33±0.16  11.78±0.18	0.60±0.01 0.49±0.02 0.47±0.01	6.72±0.15% 4.78±0.17% 4.34±0.03%	$648 \pm 51$ $397 \pm 22$ $367 \pm 14$	8.25±0.54 10.68±0.45 12.02±0.18

**Table S2.** Photovoltaic parameters for 5 hours of continuous 85 °C heating for burn-in thermal degradation test measured under one-sun test condition (AM1.5G illumination at 100 mW cm<sup>-2</sup> for both PTB7-Th:PC<sub>71</sub>BM fullerene and PTB7-Th:ITIC non-fullerene based devices obtained from at least 5 devices.

Degradation Time for PTB7-						
Th:PC <sub>71</sub> BM Devices	$V_{OC}(V)$	J <sub>SC</sub> (mA/cm <sup>2</sup> )	FF	PCE	RSH (Ω cm <sup>2</sup> )	RS (Ω cm²)
0Н	0.821 ± 0.004	14.48 ± 0.71	0.61 ± 0.01	7.25 ± 0.24%	522 ± 50	$5.98 \pm 0.25$
1Н	0.818 ± 0.010	11.80 ± 0.84	0.47 ± 0.04	4.58 ± 0.49%	251 ± 45	$9.46 \pm 1.30$
2Н	0.821 ± 0.005	11.98 ± 0.87	0.49 ± 0.02	4.85 ± 0.44%	271 ± 18	$9.07 \pm 0.84$
3Н	0.801 ± 0.009	12.42 ± 0.90	0.50 ± 0.04	4.95 ± 0.57%	275 ± 27	$8.94 \pm 1.37$
4Н	0.812 ± 0.005	12.34 ± 0.96	0.51 ± 0.02	5.14 ± 0.53%	303 ± 20	$9.02 \pm 1.23$
5Н	$0.800 \pm 0.005$	12.44 ± 0.94	0.52 ± 0.02	5.22 ± 0.50%	325 ± 17	$8.50 \pm 1.01$
Degradation Time for PTB7- Th:ITIC Devices	V <sub>oc</sub> (V)	J <sub>SC</sub> (mA/cm <sup>2</sup> )	FF	PCE	RSH (Ω cm²)	RS (Ω cm <sup>2</sup> )
Time for PTB7- Th:ITIC	V <sub>OC</sub> (V)  0.831 ± 0.002		0.60 ± 0.00	PCE 6.84 ± 0.30%	RSH (Ω cm²)	RS (Ω cm <sup>2</sup> ) $8.47 \pm 0.32$
Time for PTB7- Th:ITIC Devices	0.831 ±	(mA/cm <sup>2</sup> )	0.60 ±	6.84 ±		
Time for PTB7-Th:ITIC Devices	0.831 ± 0.002 0.831 ±	(mA/cm <sup>2</sup> )  13.75 ± 0.49	0.60 ± 0.00 0.55 ±	6.84 ± 0.30% 4.41 ±	666±13	$8.47 \pm 0.32$
Time for PTB7-Th:ITIC Devices  0H	0.831 ± 0.002 0.831 ± 0.003 0.829 ±	$(mA/cm^{2})$ $13.75 \pm 0.49$ $9.70 \pm 0.41$	$0.60 \pm 0.00$ $0.55 \pm 0.01$ $0.53 \pm$	6.84 ± 0.30% 4.41 ± 0.29% 4.30 ±	666±13 342±39	$8.47 \pm 0.32$ $9.21 \pm 0.41$
Time for PTB7-Th:ITIC Devices  OH  1H  2H	0.831 ± 0.002 0.831 ± 0.003 0.829 ± 0.002 0.814 ±	$(mA/cm^{2})$ $13.75 \pm 0.49$ $9.70 \pm 0.41$ $9.71 \pm 0.36$	$0.60 \pm 0.00$ $0.55 \pm 0.01$ $0.53 \pm 0.01$ $0.53 \pm 0.01$	6.84 ± 0.30% 4.41 ± 0.29% 4.30 ± 0.24%	666±13 342±39 299±17	$8.47 \pm 0.32$ $9.21 \pm 0.41$ $9.89 \pm 0.43$

**Table S3.** Parameters including effective voltage  $V_{\rm eff}$ , Series resistance  $R_{\rm s}$  and voltage loss term B that used to calculate the carrier recombination resistance for for both PTB7-Th:PC<sub>71</sub>BM fullerene and PTB7-Th:ITIC non-fulleren based fresh, photo-degraded and thermal-degraded devices. ( $V_{\rm eff}$  is extracted from the Figue 9 that equals to the voltage value for the minimum differential diode ideality ideality factor and  $R_{\rm s}$  is measured by EIS characterisaiton under the dark condion)

Devices	$V_{eff}(V)$	R <sub>s</sub> (Ω cm <sup>2</sup> )	B (V)
Fresh PTB7-Th:PC71BM	0.752	0.91	0.013
Photo-degraded PTB7- Th:PC71BM	0.681	0.93	0.012
Thermal-degraded PTB7- Th:PC71BM	0.772	1.08	0.013
Fresh PTB7-Th:ITIC	0.691	1.10	0.015
Photo-degraded PTB7- Th:ITIC	0.772	0.83	0.009
Thermal-degraded PTB7- Th:ITIC	0.722	1.02	0.010